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	Application No.	Applicant(s)			
	10/619,998	KIM ET AL.			
Notice of Allowability	Examiner	Art Unit			
	Bradley K Smith	2824			
The MAILING DATE of this communication appeal All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT R of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in this ap or other appropriate communication IGHTS. This application is subject to	plication. If not included n will be mailed in due co	ourse. <b>THIS</b>		
1. This communication is responsive to					
2. ⊠ The allowed claim(s) is/are <u>1-14</u> .					
3. $\boxtimes$ The drawings filed on <u>14 July 2003</u> are accepted by the Ex	kaminer.				
4.					
7. DEPOSIT OF and/or INFORMATION about the deposit of BIOLOGICAL MATERIAL must be submitted. Note the attached Examiner's comment regarding REQUIREMENT FOR THE DEPOSIT OF BIOLOGICAL MATERIAL.					
Attachment(s)  1. ☑ Notice of References Cited (PTO-892)	5.	• • • • • • • • • • • • • • • • • • • •	152)		
2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948)		<ol> <li>Interview Summary (PTO-413), Paper No./Mail Date</li> </ol>			
3. Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date	ment/Comment				
Examiner's Comment Regarding Requirement for Deposit     of Riological Material		8. \( \subseteq \text{Examiner's Statement of Reasons for Allowance} \)			
of Biological Material	9. A Other search notes.	RICHARD ELMS RVISORY PATENT EXAM CHNOLOGY CENTER 280	INER		

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## **DETAILED ACTION**

## Allowable Subject Matter

- 1. Claims 1-14 are allowed.
- 2. The following is an examiner's statement of reasons for allowance: the prior art of record neither teaches nor suggests the semiconductor memory device tunnel insulating layer and floating gate electrodes interposed between the cell line patterns and the active regions, a plurality of control gate lines, each disposed adjacent to a sidewall of the cell line patterns; a dummy region interposed between the cell region and the peripheral circuit region; and at least one dummy line pattern which is disposed in the dummy region; wherein each of the cell line patterns comprises a couple of spacer lines and a source line; wherein the couple of spacer lines are comprised of a plane sidewall and a curved sidewall, and wherein the source line is interposed between a couple of spacer lines and electrically connected to the active region between a couple of spacer lines (claims 1-13) or the method of forming a control gate insulating layer, a control gate conductive layer and an oxidation layer on a substrate, the substrate having a cell regions a dummy region, and a peripheral circuit region, the dummy region being interposed between the cell region and the peripheral region; forming a plurality of cell line patterns in the cell region; forming a plurality of dummy line patterns in the dummy region, wherein a distance between a dummy line pattern and an adjacent cell line pattern is the same as the distance between cell line patterns, and forming a control gate insulating layer and an oxidation layer and chemically mechanically polishing these layers (claim 14).

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Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

## Conclusion

3. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. Araki et al. (US Patent 6,621,117) disclose a semiconductor device with a memory cell and peripheral circuitry with a dummy electrode. Ryu et al. (US Pregrant Publication 2004/0027861) disclose a method of manufacturing a split gate flash memory device.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Bradley K Smith whose telephone number is (571) 272-1884. The examiner can normally be reached on 10-6 Monday through Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Richard Elms can be reached on (571) 272-1869. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

BKS